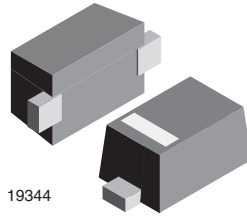


Single-Line ESD-Protection Diode in SOD-523



20278



19344

MARKING (example only)



20279

Bar = cathode marking

X = date code

Y = type code (see table below)

DESIGN SUPPORT TOOLS [click logo to get started](#)



FEATURES

- Compact SOD-523 package
- Low package height < 0.7 mm
- 1-line unidirectional ESD-protection
- AEC-Q101 qualified available
- Working range 1 V to 33 V
- ESD immunity acc. IEC 61000-4-2
±15 kV to ±30 kV contact discharge
±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
- soldering can be checked by standard vision inspection
- AOI = Automated Optical Inspection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION					
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	ENVIRONMENTAL AND QUALITY CODE			ORDERING CODE (EXAMPLE)
		RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	8K PER 7" REEL (8 mm TAPE)	
		GREEN		MOQ = 8K/BOX	
VESD05C1-02V	-	G	3	-08	VESD05C1-02V-G3-08
VESD05C1-02V	H	G	3	-08	VESD05C1-02VHG3-08

PACKAGE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
VESD01C1-02V	SOD-523	. V	1.32 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C
VESD03C1-02V		. B				
VESD05C1-02V		. C				
VESD08C1-02V		. D				
VESD012C1-02V		. E				
VESD016C1-02V		. G				
VESD026C1-02V		. X				
VESD033C1-02V		A				



ABSOLUTE MAXIMUM RATINGS VESD01C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	14.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD03C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	11.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD05C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	8.7	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD08C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	6.60	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C



ABSOLUTE MAXIMUM RATINGS VESD12C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	4.4	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD16C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	3.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD26C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	2.1	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	20	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		20	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD33C1-02V (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	1.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	15	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		15	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C



ELECTRICAL CHARACTERISTICS VESD01C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	1	V
Reverse voltage	at $I_R = 100\text{ }\mu\text{A}$	V_R	1	1.2	-	V
Reverse current	at $V_R = 1\text{ V}$	I_R	-	20	100	μA
Reverse breakdown voltage	at $I_R = 20\text{ mA}$	V_{BR}	2.5	2.65	2.8	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 14.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	6.2	6.9	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 14.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	3	3.92	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.13	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	153	192	230	pF

ELECTRICAL CHARACTERISTICS VESD03C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	3	V
Reverse voltage	at $I_R = 20\text{ }\mu\text{A}$	V_R	3	-	-	V
Reverse current	at $V_R = 3\text{ V}$	I_R	-	8	20	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	4.4	4.65	4.9	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 11.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	7.8	8.70	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 11.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	2.6	3.32	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.19	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	89	112	135	pF

ELECTRICAL CHARACTERISTICS VESD05C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	V_R	5	-	-	V
Reverse current	at $V_R = 5\text{ V}$	I_R	-	0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	6.85	7.26	7.65	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 8.7\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	10.3	11.5	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 8.7\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	2.2	2.74	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.2	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	53	67	81	pF



ELECTRICAL CHARACTERISTICS VESD08C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V
Reverse voltage	at $I_R = 0.1\text{ }\mu\text{A}$	V_R	8	-	-	V
Reverse current	at $V_R = 8\text{ V}$	I_R	-	0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	9.5	10	10.5	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 6.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	13.7	15.3	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 6.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	1.9	2.32	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.23	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	37	47	57	pF

ELECTRICAL CHARACTERISTICS VESD12C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V
Reverse voltage	at $I_R = 0.1\text{ }\mu\text{A}$	V_R	12	-	-	V
Reverse current	at $V_R = 12\text{ V}$	I_R	-	0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	13.9	14.7	15.5	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 4.4\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	20.5	22.7	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 4.4\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	1.6	1.88	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.4	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	26	33	40	pF

ELECTRICAL CHARACTERISTICS VESD16C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	16	V
Reverse voltage	at $I_R = 0.1\text{ }\mu\text{A}$	V_R	16	-	-	V
Reverse current	at $V_R = 16\text{ V}$	I_R	-	0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	17	17.9	18.8	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 3.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	25.3	28	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 3.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	1.5	1.72	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	0.53	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	21	27	33	pF



ELECTRICAL CHARACTERISTICS VESD26C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	26	V
Reverse voltage	at $I_R = 0.1\text{ }\mu\text{A}$	V_R	26	-	-	V
Reverse current	at $V_R = 26\text{ V}$	I_R	-	< 0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	27.6	29.1	30.6	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 2.1\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	43	48	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 2.1\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	1.3	1.42	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	1.9	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	14	17.5	21	pF

ELECTRICAL CHARACTERISTICS VESD33C1-02V ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	33	V
Reverse voltage	at $I_R = 0.1\text{ }\mu\text{A}$	V_R	33	-	-	V
Reverse current	at $V_R = 33\text{ V}$	I_R	-	< 0.01	0.1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	35.5	37.4	39.3	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 1.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_C	-	56	62.5	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$, $t_p = 300\text{ }\mu\text{s}$	V_F	0.9	1.1	1.2	V
	at $I_{PP} = I_{PPM} = 1.6\text{ A}$, $t_p = 8/20\text{ }\mu\text{s}$	V_F	-	1.22	1.32	V
Dynamic resistance	$t_p = 100\text{ ns}$ (TLP; pin 2-1)	r_{dyn}	-	3.6	-	Ω
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	12	15	18	pF



Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω / 150 pF)



Fig. 4 - Typical Capacitance vs. Reverse Voltage



Fig. 2 - 8/20 μs Peak Pulse Current Wave Form acc. IEC 61000-4-5



Fig. 5 - Typical Reverse Voltage vs. Reverse Current



Fig. 3 - Typical Peak Clamping Voltage vs. Peak Pulse Current



Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current



Fig. 7 - Typical Forward Voltage vs. Forward Current



Fig. 8 - Typical Forward Voltage vs. Forward Current

PACKAGE DIMENSIONS in millimeters (Inches): SOD-523



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 23093



CARRIER TAPE SOD-523



S8-V-3717.03-005 (4)
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ORIENTATION IN CARRIER TAPE SOD-523



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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